



# STW9NA60 STH9NA60FI

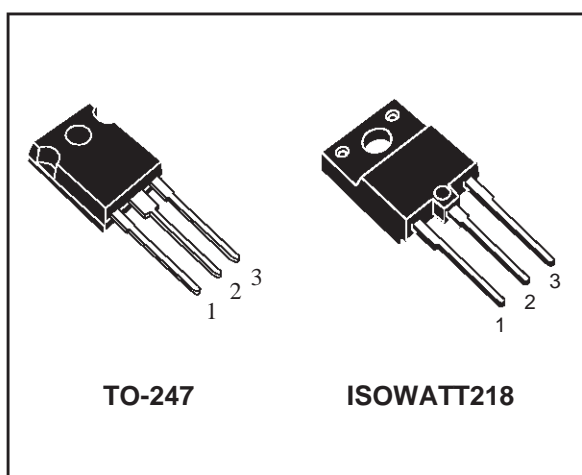
## N - CHANNEL ENHANCEMENT MODE FAST POWER MOS TRANSISTOR

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STW9NA60	600 V	< 0.8 Ω	9.5 A
STH9NA60FI	600 V	< 0.8 Ω	6.4 A

- TYPICAL R<sub>DS(on)</sub> = 0.69 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD

### APPLICATIONS

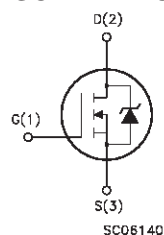
- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



TO-247

ISOWATT218

### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW9NA60	STH9NA60FI	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	600		V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	600		V
V <sub>GS</sub>	Gate-source Voltage	± 30		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	6.4	9.5	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	4	6	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	38	38	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	70	160	W
	Derating Factor	0.56	1.28	W/°C
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	—	4000	V
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

**STW9NA60-STH9NA60FI****THERMAL DATA**

			TO-247	ISOWATT218	
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	0.78	1.78	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	30		°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ	0.1		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300		°C

**AVALANCHE CHARACTERISTICS**

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	9.5	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	450	mJ

**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)**OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	600			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>c</sub> = 100 °C			25 250	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 30 V			± 100	nA

**ON (\*)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2.25	3	3.75	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 4.5 A		0.69	0.8	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	9			A

**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 4.5A	5	8.3		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		1800	2350	pF
C <sub>oss</sub>	Output Capacitance			230	300	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			65	85	pF

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 300\text{ V}$ $I_D = 4.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		21	30	ns
$t_r$	Rise Time			32	45	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 480\text{ V}$ $I_D = 9\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		180		A/ $\mu\text{s}$
$Q_g$	Total Gate Charge	$V_{DD} = 480\text{ V}$ $I_D = 9\text{ A}$ $V_{GS} = 10\text{ V}$		75	100	nC
$Q_{gs}$	Gate-Source Charge			11		nC
$Q_{gd}$	Gate-Drain Charge			36		nC

**SWITCHING OFF**

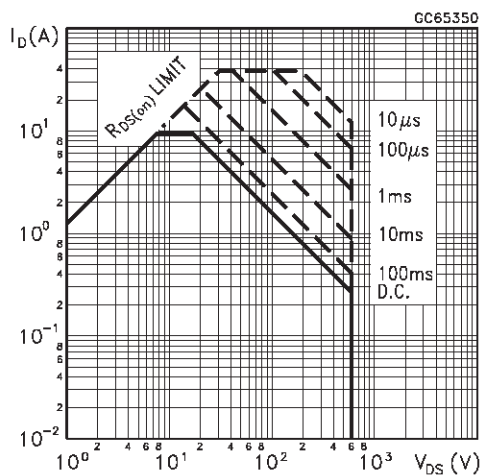
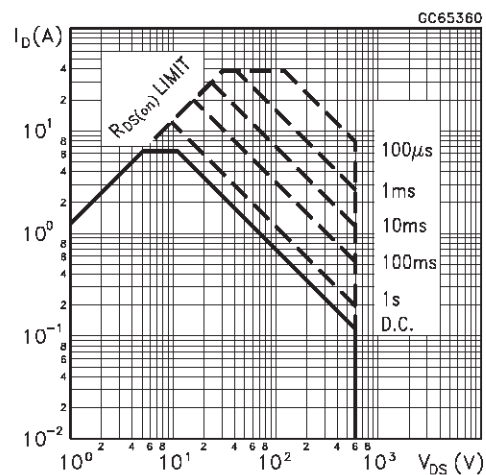
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(off)}$	Off-voltage Rise Time	$V_{DD} = 480\text{ V}$ $I_D = 9\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		16	23	ns
$t_f$	Fall Time			18	25	ns
$t_c$	Cross-over Time			26	35	ns

**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				9.5	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				38	A
$V_{SD}(\ast)$	Forward On Voltage	$I_{SD} = 9.5\text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 9.5\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		660		ns
$Q_{rr}$	Reverse Recovery Charge			12		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			36		A

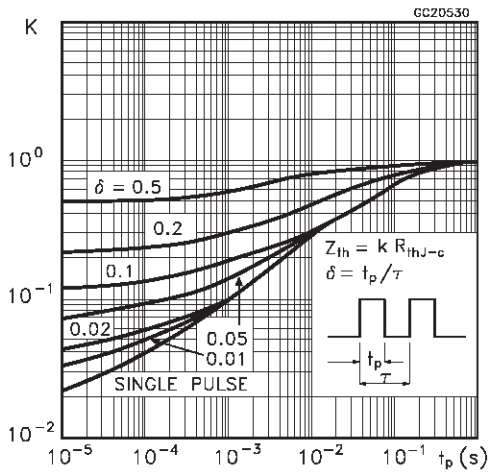
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

(•) Pulse width limited by safe operating area

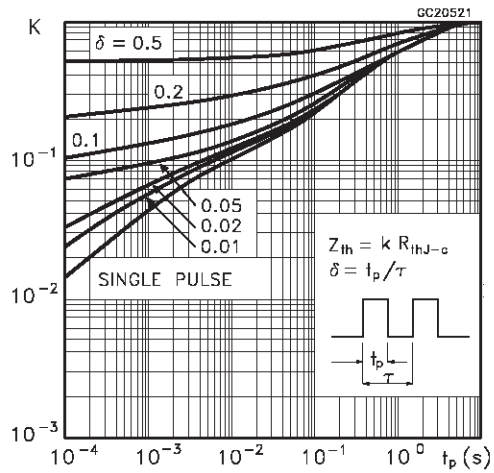
**Safe Operating Area for TO-247****Safe Operating Area for ISOWATT218**

# STW9NA60-STH9NA60FI

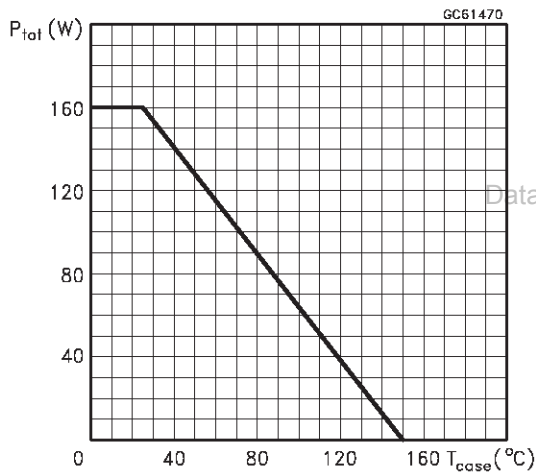
Thermal Impedance for TO-247



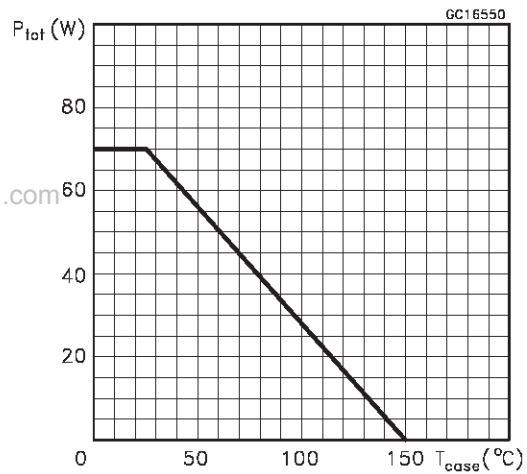
Thermal Impedance for ISOWATT218



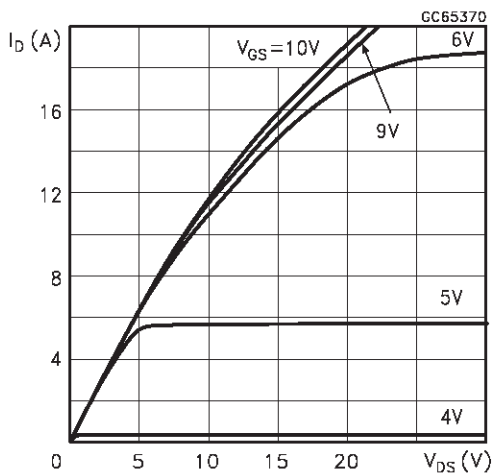
Derating Curve for TO-247



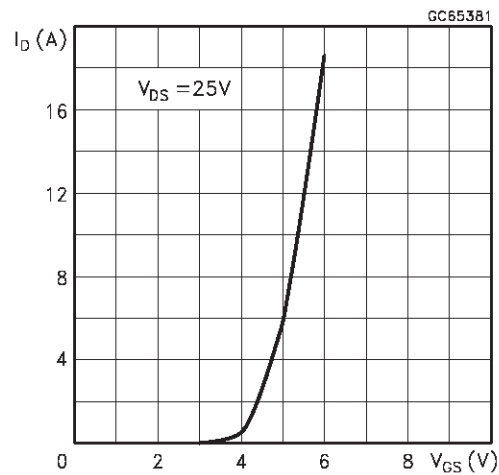
Derating Curve for ISOWATT218



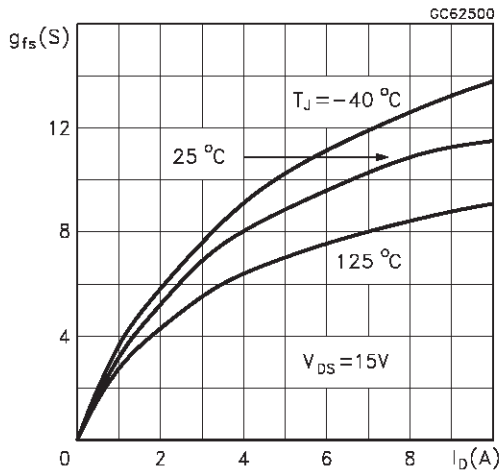
Output Characteristics



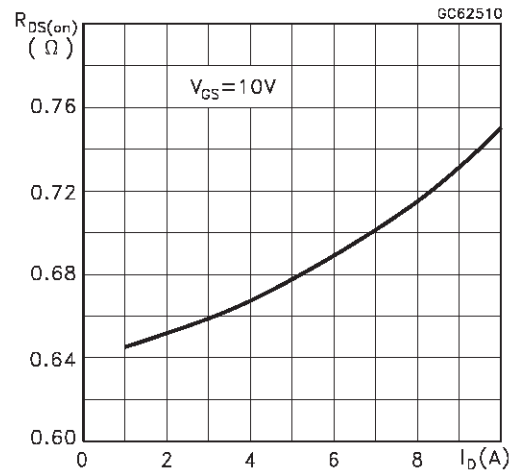
Transfer Characteristics



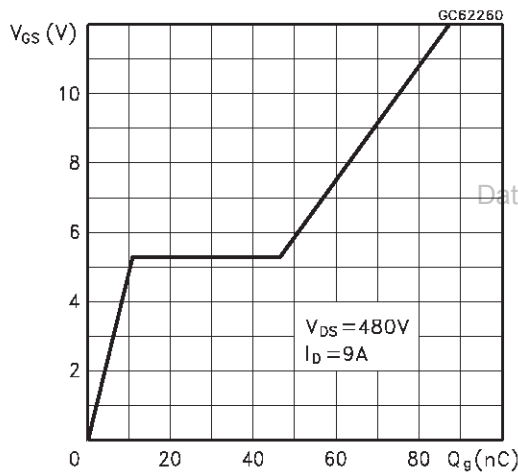
Transconductance



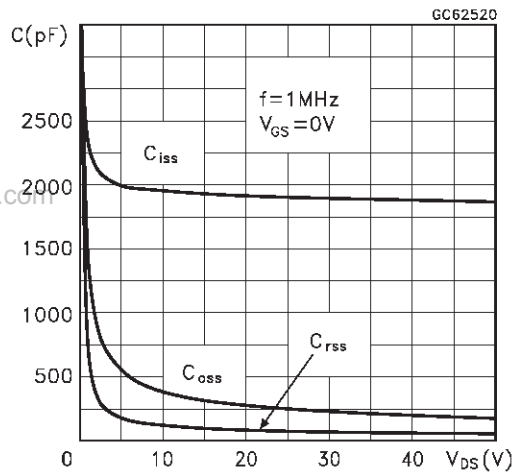
Static Drain-source On Resistance



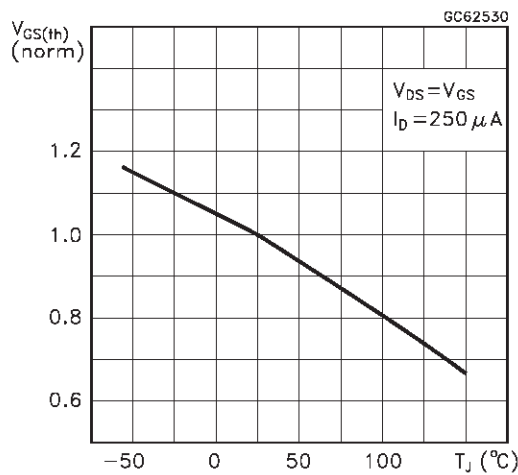
Gate Charge vs Gate-source Voltage



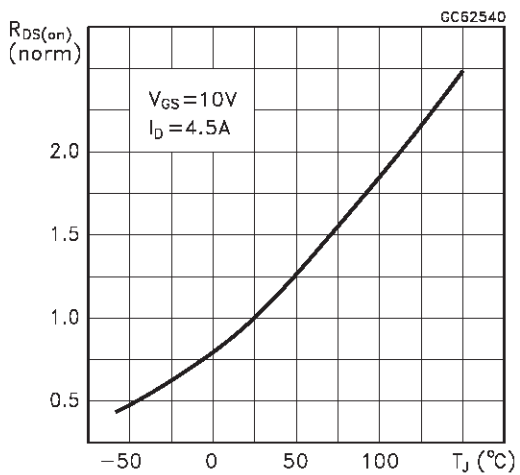
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature

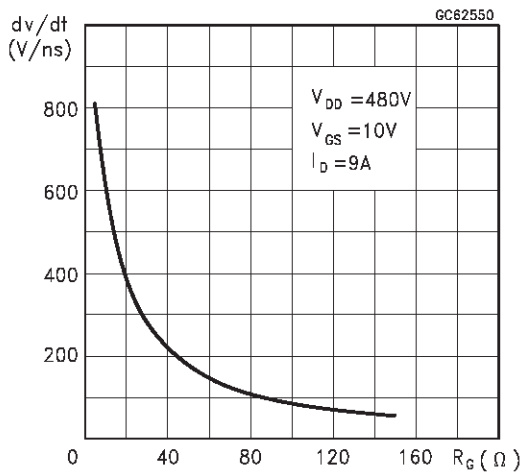


Normalized On Resistance vs Temperature

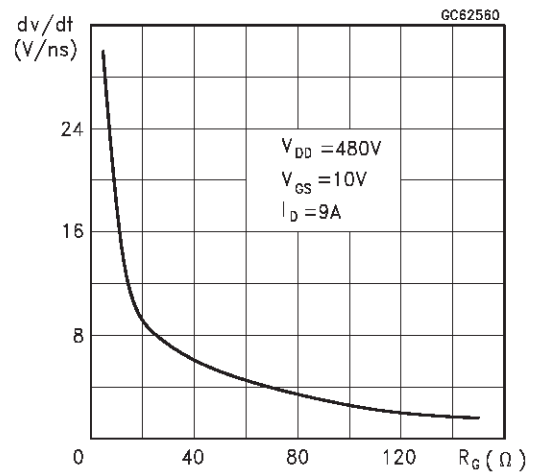


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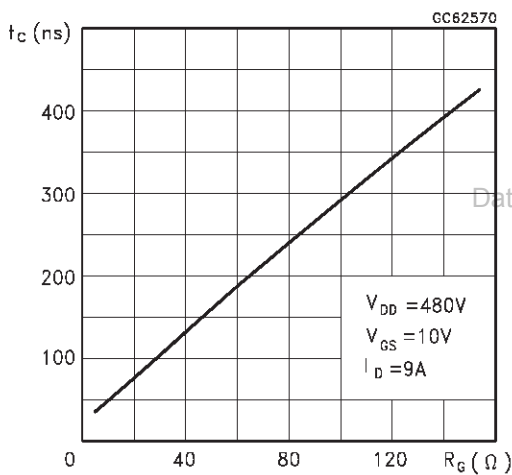
Turn-on Current Slope



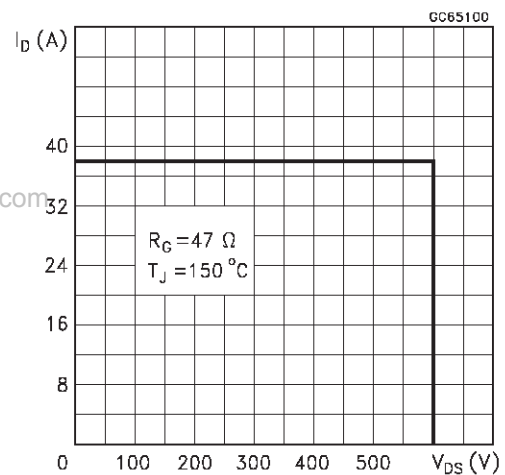
Turn-off Drain-source Voltage Slope



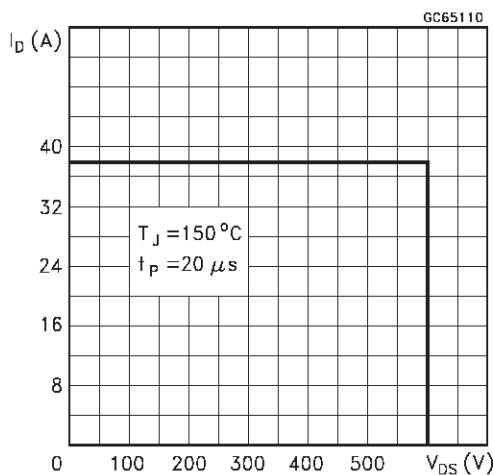
Cross-over Time



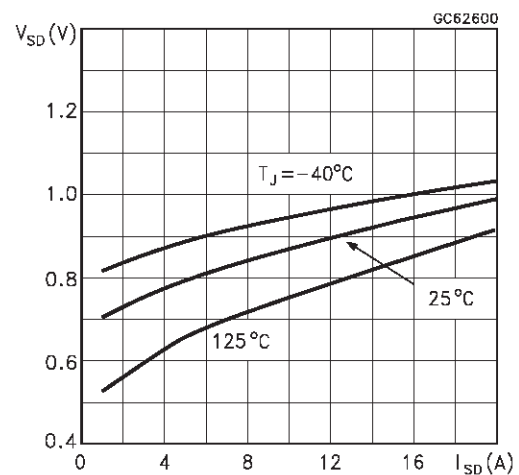
Switching Safe Operating Area



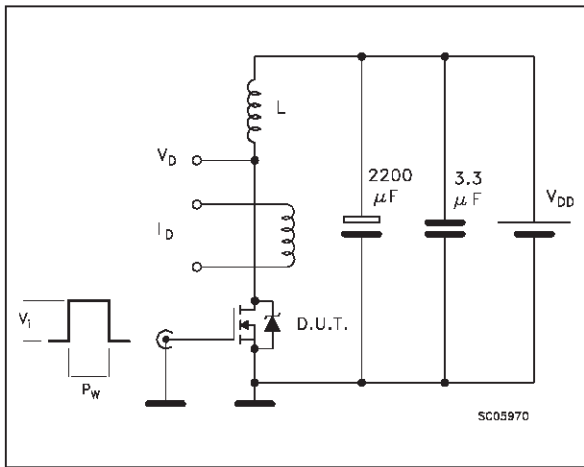
Accidental Overload Area



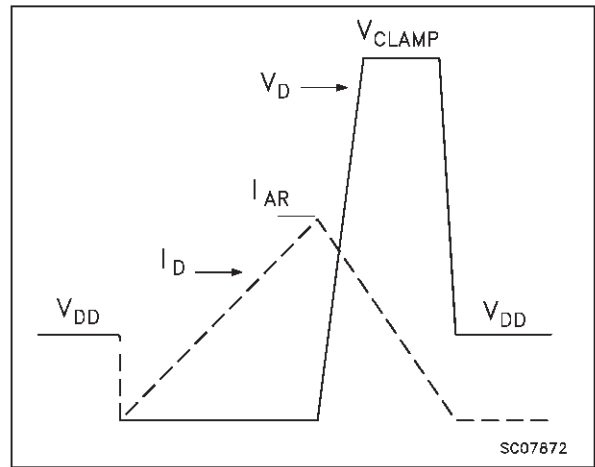
Source-drain Diode Forward Characteristics



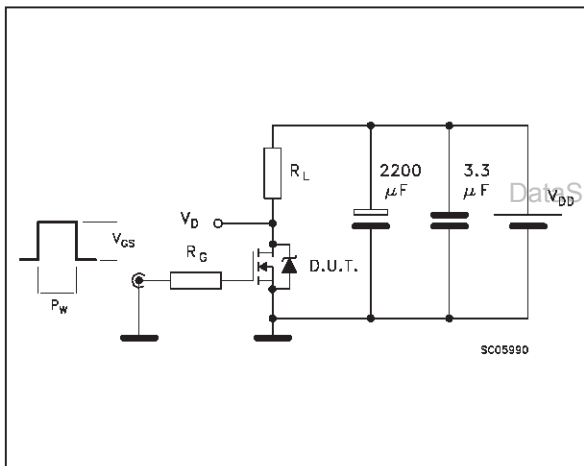
**Fig. 1: Unclamped Inductive Load Test Circuit**



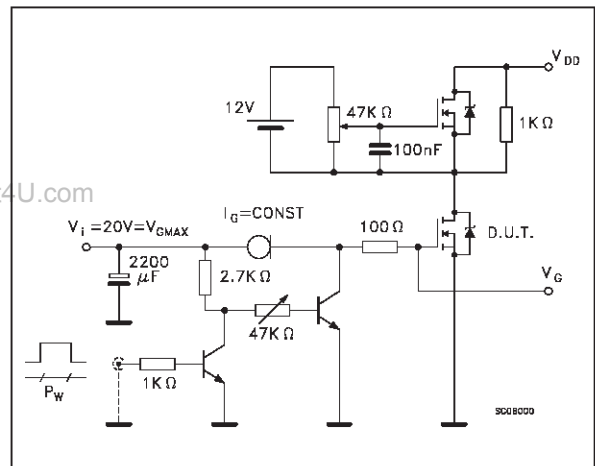
**Fig. 2: Unclamped Inductive Waveform**



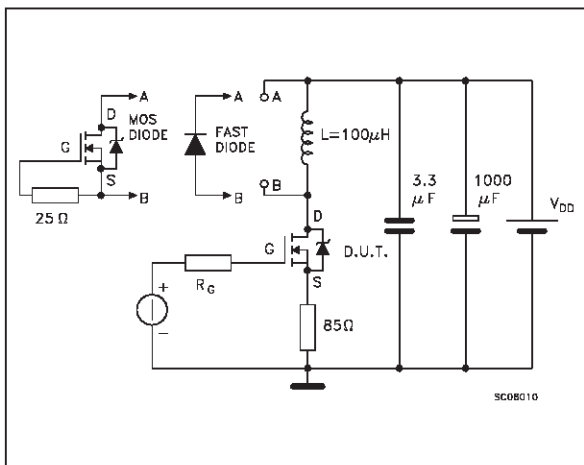
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge test Circuit**



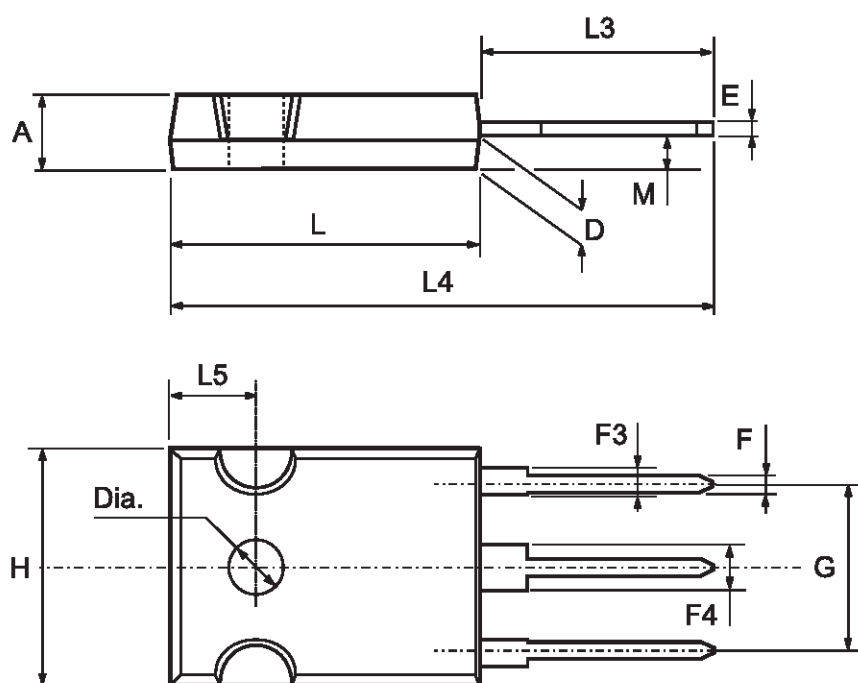
**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



## STW9NA60-STH9NA60FI

## TO-247 MECHANICAL DATA

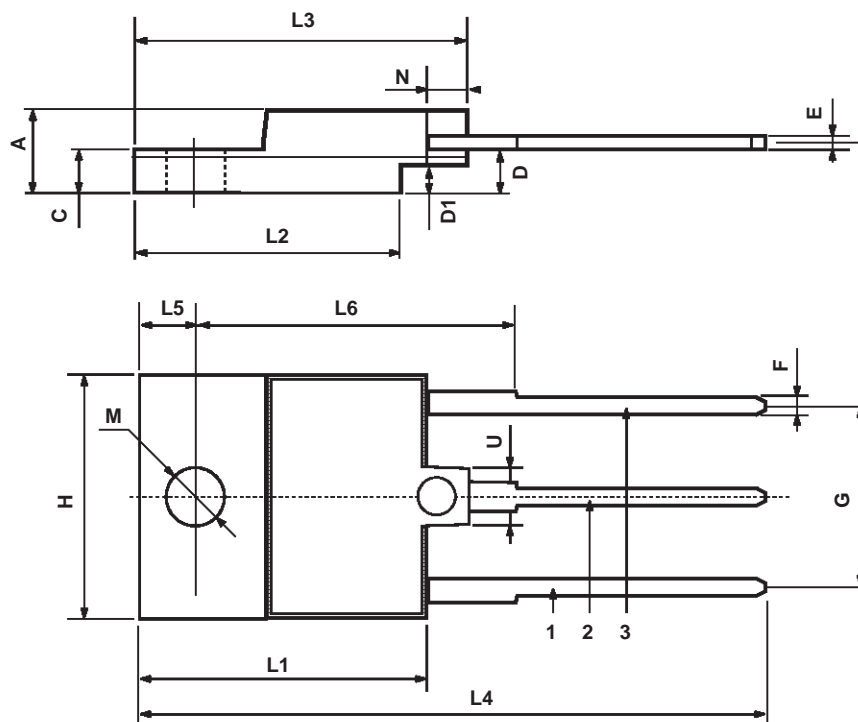
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559	0.413	0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118
Dia	3.55		3.65	0.140		0.144





## ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.75		1	0.029		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	



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## STW9NA60-STH9NA60FI

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